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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I ² C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, DMA, I ² S, LCD, POR, PWM, WDT
Number of I/O	115
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 40x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	144-LQFP
Supplier Device Package	-
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l162zct6

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2.1 Device overview

Table 2. Ultra-low-power STM32L162xC/C-A device features and peripheral counts

Peripheral		STM32L162RC-A	STM32L162VC-A	STM32L162QC	STM32L162ZC
Flash (Kbytes)		256			
Data EEPROM (Kbytes)		8			
RAM (Kbytes)		32			
AES		1			
Timers	32 bit	1			
	General-purpose	6			
	Basic	2			
Communication interfaces	SPI	8(3) ⁽¹⁾			
	I ² S	2			
	I ² C	2			
	USART	3			
	USB	1			
GPIOs		51	83	109	115
Operation amplifiers		2			
12-bit synchronized ADC Number of channels		1 21	1 25	1 40	1 40
12-bit DAC Number of channels		2 2			
LCD (STM32L152xx devices only) COM x SEG		1 4x32 or 8x28	1 4x44 or 8x40		
Comparators		2			
Capacitive sensing channels		23			
Max. CPU frequency		32 MHz			
Operating voltage		1.8 V to 3.6 V (down to 1.65 V at power-down) with BOR option 1.65 V to 3.6 V without BOR option			
Operating temperatures		Ambient operating temperature: -40 °C to 85 °C / -40 °C to 105 °C Junction temperature: -40 to + 110 °C			
Packages		LQFP64	LQFP100	UFBGA132	LQFP144

1. 5 SPIs are USART configured in synchronous mode emulating SPI master.

Table 5. Functionalities depending on the working mode (from Run/active down to standby)

Ips	Run/Active	Sleep	Low-power Run	Low-power Sleep	Stop		Standby	
						Wakeup capability		Wakeup capability
CPU	Y	--	Y	--	--	--	--	--
Flash	Y	Y	Y	Y	--	--	--	--
RAM	Y	Y	Y	Y	Y	--	--	--
Backup Registers	Y	Y	Y	Y	Y	--	Y	--
EEPROM	Y	Y	Y	Y	Y	--	--	--
Brown-out rest (BOR)	Y	Y	Y	Y	Y	Y	Y	--
DMA	Y	Y	Y	Y	--	--	--	--
Programmable Voltage Detector (PVD)	Y	Y	Y	Y	Y	Y	Y	--
Power On Reset (POR)	Y	Y	Y	Y	Y	Y	Y	--
Power Down Rest (PDR)	Y	Y	Y	Y	Y	--	Y	--
High Speed Internal (HSI)	Y	Y	--	--	--	--	--	--
High Speed External (HSE)	Y	Y	--	--	--	--	--	--
Low Speed Internal (LSI)	Y	Y	Y	Y	Y	--	Y	--
Low Speed External (LSE)	Y	Y	Y	Y	Y	--	Y	--
Multi-Speed Internal (MSI)	Y	Y	Y	Y	--	--	--	--
Inter-Connect Controller	Y	Y	Y	Y	--	--	--	--
RTC	Y	Y	Y	Y	Y	Y	Y	--
RTC Tamper	Y	Y	Y	Y	Y	Y	Y	Y
Auto WakeUp (AWU)	Y	Y	Y	Y	Y	Y	Y	Y
LCD	Y	Y	Y	Y	Y	--	--	--
USB	Y	Y	--	--	--	Y	--	--
USART	Y	Y	Y	Y	Y	(1)	--	--
SPI	Y	Y	Y	Y	--	--	--	--
I2C	Y	Y	Y	Y	--	(1)	--	--

Table 8. STM32L162xC/C-A pin definitions (continued)

Pins					Pin name	Pin Type ⁽¹⁾	I / O structure	Main function ⁽²⁾ (after reset)	Pin functions	
LQFP144	UFBGA132	LQFP100	LQFP64	WL CSP64					Alternate functions	Additional functions
7	C1	7	2	C8	PC13-WKUP2	I/O	FT	PC13	-	WKUP2/ RTC_TAMP1/ RTC_TS/ RTC_OUT
8	D1	8	3	B8	PC14-OSC32_IN ⁽⁴⁾	I/O	TC	PC14	-	OSC32_IN
9	E1	9	4	B7	PC15-OSC32_OUT	I/O	TC	PC15	-	OSC32_OUT
10	D6	-	-	-	PF0	I/O	FT	PF0	-	-
11	D5	-	-	-	PF1	I/O	FT	PF1	-	-
12	D4	-	-	-	PF2	I/O	FT	PF2	-	-
13	E4	-	-	-	PF3	I/O	FT	PF3	-	-
14	F3	-	-	-	PF4	I/O	FT	PF4	-	-
15	F4	-	-	-	PF5	I/O	FT	PF5	-	-
16	F2	10	-	-	V _{SS_5}	S	-	V _{SS_5}	-	-
17	G2	11	-	-	V _{DD_5}	S	-	V _{DD_5}	-	-
18	G3	-	-	-	PF6	I/O	FT	PF6	TIM5_CH1/TIM5_ETR	ADC_IN27
19	G4	-	-	-	PF7	I/O	FT	PF7	TIM5_CH2	ADC_IN28/ COMP1_INP
20	H4	-	-	-	PF8	I/O	FT	PF8	TIM5_CH3	ADC_IN29/ COMP1_INP
21	J6	-	-	-	PF9	I/O	FT	PF9	TIM5_CH4	ADC_IN30/ COMP1_INP
22	-	-	-	-	PF10	I/O	FT	PF10	-	ADC_IN31/ COMP1_INP
23	F1	12	5	D8	PH0-OSC_IN ⁽⁵⁾	I/O	TC	PH0	-	OSC_IN
24	G1	13	6	D7	PH1-OSC_OUT ⁽⁵⁾	I/O	TC	PH1	-	OSC_OUT
25	H2	14	7	C7	NRST	I/O	RST	NRST	-	-
26	H1	15	8	E8	PC0	I/O	FT	PC0	LCD_SEG18	ADC_IN10/ COMP1_INP

Table 8. STM32L162xC/C-A pin definitions (continued)

Pins					Pin name	Pin Type ⁽¹⁾	I / O structure	Main function ⁽²⁾ (after reset)	Pin functions	
LQFP144	UFBGA132	LQFP100	LQFP64	WLCSP64					Alternate functions	Additional functions
96	E12	63	37	E1	PC6	I/O	FT	PC6	TIM3_CH1/I2S2_MCK/ LCD_SEG24	-
97	E11	64	38	E2	PC7	I/O	FT	PC7	TIM3_CH2/I2S3_MCK/ LCD_SEG25	-
98	E10	65	39	E3	PC8	I/O	FT	PC8	TIM3_CH3/LCD_SEG26	-
99	D12	66	40	D1	PC9	I/O	FT	PC9	TIM3_CH4/LCD_SEG27	-
100	D11	67	41	E4	PA8	I/O	FT	PA8	USART1_CK/MCO/ LCD_COM0	-
101	D10	68	42	D2	PA9	I/O	FT	PA9	USART1_TX / LCD_COM1	-
102	C12	69	43	D3	PA10	I/O	FT	PA10	USART1_RX / LCD_COM2	-
103	B12	70	44	C1	PA11	I/O	FT	PA11	USART1_CTS/ SPI1_MISO	USB_DM
104	A12	71	45	C2	PA12	I/O	FT	PA12	USART1_RTS/ SPI1_MOSI	USB_DP
105	A11	72	46	D4	PA13	I/O	FT	JTMS-SWDIO	JTMS-SWDIO	-
106	C11	73	-	-	PH2	I/O	FT	PH2	-	-
107	F11	74	47	B1	V _{SS_2}	S	-	V _{SS_2}	-	-
108	G11	75	48	A1	V _{DD_2}	S	-	V _{DD_2}	-	-
109	A10	76	49	B2	PA14	I/O	FT	JTCK-SWCLK	JTCK-SWCLK	-
110	A9	77	50	C3	PA15	I/O	FT	JTDI	TIM2_CH1_ETR/ SPI1_NSS/SPI3_NSS/ I2S3_WS/LCD_SEG17/ JTDI	-
111	B11	78	51	A2	PC10	I/O	FT	PC10	SPI3_SCK/I2S3_CK/ USART3_TX/ LCD_SEG28/LCD_SEG40/ LCD_COM4	-
112	C10	79	52	B3	PC11	I/O	FT	PC11	SPI3_MISO/USART3_RX/ LCD_SEG29/LCD_SEG41/ LCD_COM5	-

Table 9. Alternate function input/output (continued)

Port name	Digital alternate function number														
	AFIO0	AFIO1	AFIO2	AFIO3	AFIO4	AFIO5	AFIO6	AFIO7	AFIO8	..	AFIO11	AFIO12	..	AFIO14	AFIO15
	Alternate function														
	SYSTEM	TIM2	TIM3/4/5	TIM9/10/11	I2C1/2	SPI1/2	SPI3	USART1/2/3	-		LCD	-		CPRI	SYSTEM
PG5	-	-	-	-	-	-	-	-	-		-			-	EVENT OUT
PG6	-	-	-	-	-	-	-	-	-		-	-		-	EVENT OUT
PG7	-	-	-	-	-	-	-	-	-		-	-		-	EVENT OUT
PG8	-	-	-	-	-	-	-	-	-		-	-		-	EVENT OUT
PG9	-	-	-	-	-	-	-	-	-		-			-	EVENT OUT
PG10	-	-	-	-	-	-	-	-	-		-			-	EVENT OUT
PG11	-	-	-	-	-	-	-	-	-		-	-		-	EVENT OUT
PG12	-	-	-	-	-	-	-	-	-		-			-	EVENT OUT
PG13	-	-	-	-	-	-	-	-	-		-			-	EVENT OUT
PG14	-	-	-	-	-	-	-	-	-		-			-	EVENT OUT
PG15	-	-	-	-	-	-	-	-	-		-	-		-	EVENT OUT
PH0OSC_IN	-	-	-	-	-	-	-	-	-		-	-		-	-
PH1OSC_OUT	-	-	-	-	-	-	-	-	-		-	-		-	-
PH2	-	-	-	-	-	-	-	-	-		-			-	-

4. Positive current injection is not possible on these I/Os. A negative injection is induced by $V_{IN} < V_{SS}$. $I_{INJ(PIN)}$ must never be exceeded. Refer to [Table 10](#) for maximum allowed input voltage values.
5. A positive injection is induced by $V_{IN} > V_{DD}$ while a negative injection is induced by $V_{IN} < V_{SS}$. $I_{INJ(PIN)}$ must never be exceeded. Refer to [Table 10: Voltage characteristics](#) for the maximum allowed input voltage values.
6. When several inputs are submitted to a current injection, the maximum $\Sigma I_{INJ(PIN)}$ is the absolute sum of the positive and negative injected currents (instantaneous values).

Table 12. Thermal characteristics

Symbol	Ratings	Value	Unit
T_{STG}	Storage temperature range	-65 to +150	°C
T_J	Maximum junction temperature	150	°C

6.3 Operating conditions

6.3.1 General operating conditions

Table 13. General operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
f_{HCLK}	Internal AHB clock frequency	-	0	32	MHz
f_{PCLK1}	Internal APB1 clock frequency	-	0	32	
f_{PCLK2}	Internal APB2 clock frequency	-	0	32	
V_{DD}	Standard operating voltage	BOR detector disabled	1.65	3.6	V
		BOR detector enabled, at power on	1.8	3.6	
		BOR detector disabled, after power on	1.65	3.6	
$V_{DDA}^{(1)}$	Analog operating voltage (ADC and DAC not used)	Must be the same voltage as $V_{DD}^{(2)}$	1.65	3.6	V
	Analog operating voltage (ADC or DAC used)		1.8	3.6	
V_{IN}	I/O input voltage	FT pins; $2.0\text{ V} \leq V_{DD}$	-0.3	5.5 ⁽³⁾	V
		FT pins; $V_{DD} < 2.0\text{ V}$	-0.3	5.25 ⁽³⁾	
		BOOT0 pin	0	5.5	
		Any other pin	-0.3	$V_{DD}+0.3$	
P_D	Power dissipation at $T_A = 85\text{ °C}$ for suffix 6 or $T_A = 105\text{ °C}$ for suffix 7 ⁽⁴⁾	UFBGA132 package	-	333	mW
		LQFP144 package	-	500	
		LQFP100 package	-	465	
		LQFP64 package	-	435	
T_A	Ambient temperature for 6 suffix version	Maximum power dissipation ⁽⁵⁾	-40	85	°C
	Ambient temperature for 7 suffix version	Maximum power dissipation	-40	105	

Table 19. Current consumption in Sleep mode

Symbol	Parameter	Conditions		f _{HCLK}	Typ	Max (1)	Unit
I _{DD(SLEEP)}	Supply current in Sleep mode, code executed from RAM, Flash switched OFF	f _{HSE} = f _{HCLK} up to 16 MHz, included f _{HSE} = f _{HCLK} /2 above 16 MHz (PLL ON) ⁽²⁾	Range3, Vcore=1.2 V VOS[1:0]=11	1	58	220	μA
				2	96	300	
				4	170	380	
			Range2, Vcore=1.5 V VOS[1:0]=10	4	210	500	
				8	400	700	
				16	810	1100	
			Range1, Vcore=1.8 V VOS[1:0]=01	8	485	800	
				16	955	1250	
				32	2100	2700	
		HSI clock source (16 MHz)	Range2, Vcore=1.5 V VOS[1:0]=10	16	835	1100	
			Range1, Vcore=1.8 V VOS[1:0]=01	32	2100	2700	
		MSI clock, 65 kHz	Range3, Vcore=1.2 V VOS[1:0]=11	0.065	18.5	72	
		MSI clock, 524 kHz		0.524	37	92	
		MSI clock, 4.2 MHz		4.2	180	273	
	Supply current in Sleep mode, Flash switched ON	f _{HSE} = f _{HCLK} up to 16 MHz, included f _{HSE} = f _{HCLK} /2 above 16MHz (PLL ON) ⁽²⁾	Range3, Vcore=1.2 V VOS[1:0]=11	1	75	250	
				2	115	300	
				4	200	380	
			Range2, Vcore=1.5 V VOS[1:0]=10	4	230	500	
				8	430	700	
				16	840	1120	
			Range1, Vcore=1.8 V VOS[1:0]=01	8	500	800	
				16	980	1300	
				32	2100	2700	
		HSI clock source (16 MHz)	Range2, Vcore=1.5 V VOS[1:0]=10	16	860	1160	
			Range1, Vcore=1.8 V VOS[1:0]=01	32	2150	2800	
		MSI clock, 65 kHz	Range3, Vcore=1.2 V VOS[1:0]=11	0.065	33,5	90	
		MSI clock, 524 kHz		0.524	53	110	
		MSI clock, 4.2 MHz		4.2	200	290	

1. Guaranteed by characterization results, unless otherwise specified.

Table 23. Typical and maximum current consumptions in Standby mode

Symbol	Parameter	Conditions		Typ	Max ⁽¹⁾	Unit
I_{DD} (Standby with RTC)	Supply current in Standby mode with RTC enabled	RTC clocked by LSI (no independent watchdog)	$T_A = -40\text{ }^{\circ}\text{C}$ to $25\text{ }^{\circ}\text{C}$ $V_{DD} = 1.8\text{ V}$	0.82	-	μA
			$T_A = -40\text{ }^{\circ}\text{C}$ to $25\text{ }^{\circ}\text{C}$	1.15	1.9	
			$T_A = 55\text{ }^{\circ}\text{C}$	1.15	2.2	
			$T_A = 85\text{ }^{\circ}\text{C}$	1.65	4	
			$T_A = 105\text{ }^{\circ}\text{C}$	2.75	8.3 ⁽²⁾	
		RTC clocked by LSE external quartz (no independent watchdog) ⁽³⁾	$T_A = -40\text{ }^{\circ}\text{C}$ to $25\text{ }^{\circ}\text{C}$ $V_{DD} = 1.8\text{ V}$	1.05	-	
			$T_A = -40\text{ }^{\circ}\text{C}$ to $25\text{ }^{\circ}\text{C}$	1.35	-	
			$T_A = 55\text{ }^{\circ}\text{C}$	1.55	-	
			$T_A = 85\text{ }^{\circ}\text{C}$	2.1	-	
			$T_A = 105\text{ }^{\circ}\text{C}$	3.3	-	
I_{DD} (Standby)	Supply current in Standby mode (RTC disabled)	Independent watchdog and LSI enabled	$T_A = -40\text{ }^{\circ}\text{C}$ to $25\text{ }^{\circ}\text{C}$	1	1.7	μA
		Independent watchdog and LSI OFF	$T_A = -40\text{ }^{\circ}\text{C}$ to $25\text{ }^{\circ}\text{C}$	0.305	0.6	
			$T_A = 55\text{ }^{\circ}\text{C}$	0.365	0.9	
			$T_A = 85\text{ }^{\circ}\text{C}$	0.66	2.75	
			$T_A = 105\text{ }^{\circ}\text{C}$	2	7 ⁽²⁾	
I_{DD} (WU from Standby)	Supply current during wakeup time from Standby mode	-	$T_A = -40\text{ }^{\circ}\text{C}$ to $25\text{ }^{\circ}\text{C}$	1	-	mA

1. Guaranteed by characterization results, unless otherwise specified.

2. Guaranteed by test in production.

3. Based on characterization done with a 32.768 kHz crystal (MC306-G-06Q-32.768, manufacturer JFVNY) with two 6.8pF loading capacitors.

On-chip peripheral current consumption

The current consumption of the on-chip peripherals is given in the following table. The MCU is placed under the following conditions:

- all I/O pins are in input mode with a static value at V_{DD} or V_{SS} (no load)
- all peripherals are disabled unless otherwise mentioned
- the given value is calculated by measuring the current consumption
 - with all peripherals clocked off
 - with only one peripheral clocked on

Table 24. Peripheral current consumption⁽¹⁾

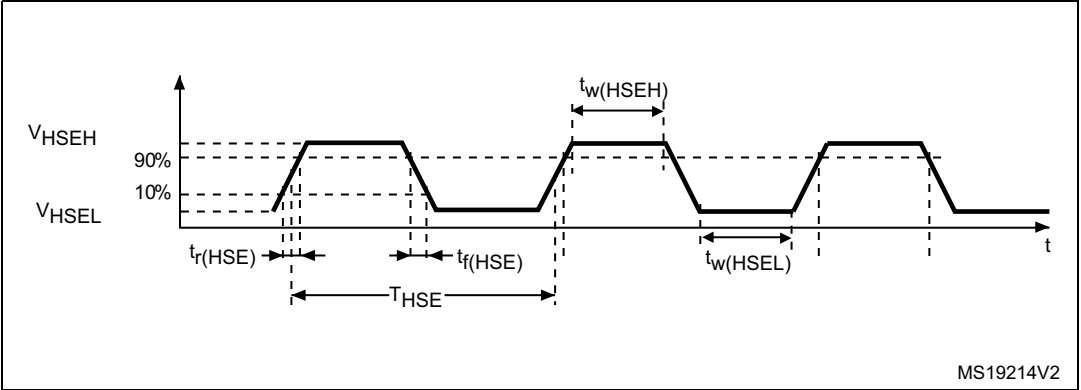
Peripheral		Typical consumption, $V_{DD} = 3.0\text{ V}$, $T_A = 25\text{ °C}$				Unit
		Range 1, $V_{CORE} = 1.8\text{ V}$ $VOS[1:0] = 01$	Range 2, $V_{CORE} = 1.5\text{ V}$ $VOS[1:0] = 10$	Range 3, $V_{CORE} = 1.2\text{ V}$ $VOS[1:0] = 11$	Low-power sleep and run	
APB1	TIM2	14.3	12.1	9.5	12.1	$\mu\text{A/MHz}$ (f_{HCLK})
	TIM3	13.8	11.7	9.2	11.7	
	TIM4	13.2	11.1	8.7	11.1	
	TIM5	17.7	14.9	11.8	14.9	
	TIM6	4.8	4.0	3.0	4.0	
	TIM7	4.7	3.9	3.0	3.9	
	LCD	5.0	4.1	3.3	4.1	
	WWDG	3.5	2.9	2.3	2.9	
	SPI2	8.9	7.4	5.8	7.4	
	SPI3	7.3	6.0	4.8	6.0	
	USART2	9.4	7.7	6.1	7.7	
	USART3	9.4	7.6	6.0	7.6	
	I2C1	8.9	7.4	5.8	7.4	
	I2C2	7.9	6.4	5.1	6.4	
	USB	21.2	18.0	14.3	18.0	
	PWR	4.0	3.2	2.5	3.2	
	DAC	6.3	5.5	4.4	5.5	
	COMP	4.9	3.9	3.2	3.9	

Table 26. High-speed external user clock characteristics⁽¹⁾ (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{HSEH}	OSC_IN input pin high level voltage	-	$0.7V_{DD}$	-	V_{DD}	V
V_{HSEL}	OSC_IN input pin low level voltage		V_{SS}	-	$0.3V_{DD}$	
$t_{w(HSEH)}$ $t_{w(HSEL)}$	OSC_IN high or low time		12	-	-	ns
$t_r(HSE)$ $t_f(HSE)$	OSC_IN rise or fall time		-	-	20	
$C_{in(HSE)}$	OSC_IN input capacitance		-	2.6	-	pF

1. Guaranteed by design.

Figure 13. High-speed external clock source AC timing diagram



Flash memory and data EEPROM

Table 35. Flash memory and data EEPROM characteristics

Symbol	Parameter	Conditions	Min	Typ	Max ⁽¹⁾	Unit
V_{DD}	Operating voltage Read / Write / Erase	-	1.65	-	3.6	V
t_{prog}	Programming/ erasing time for byte / word / double word / half-page	Erasing	-	3.28	3.94	ms
		Programming	-	3.28	3.94	
I_{DD}	Average current during the whole programming / erase operation	$T_A = 25\text{ }^{\circ}\text{C}$, $V_{DD} = 3.6\text{ V}$	-	600	900	μA
	Maximum current (peak) during the whole programming / erase operation		-	1.5	2.5	mA

1. Guaranteed by design.

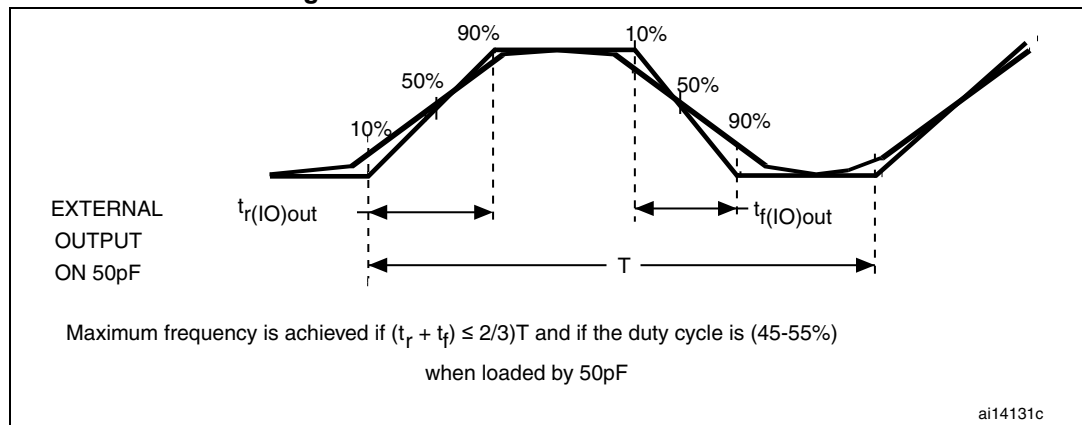
Table 36. Flash memory and data EEPROM endurance and retention

Symbol	Parameter	Conditions	Value			Unit
			Min ⁽¹⁾	Typ	Max	
$N_{CYC}^{(2)}$	Cycling (erase / write) Program memory	$T_A = -40\text{ }^{\circ}\text{C}$ to $105\text{ }^{\circ}\text{C}$	10	-	-	kcycles
	Cycling (erase / write) EEPROM data memory		300	-	-	
$t_{RET}^{(2)}$	Data retention (program memory) after 10 kcycles at $T_A = 85\text{ }^{\circ}\text{C}$	$T_{RET} = +85\text{ }^{\circ}\text{C}$	30	-	-	years
	Data retention (EEPROM data memory) after 300 kcycles at $T_A = 85\text{ }^{\circ}\text{C}$	$T_{RET} = +85\text{ }^{\circ}\text{C}$	30	-	-	
	Data retention (program memory) after 10 kcycles at $T_A = 105\text{ }^{\circ}\text{C}$	$T_{RET} = +105\text{ }^{\circ}\text{C}$	10	-	-	
	Data retention (EEPROM data memory) after 300 kcycles at $T_A = 105\text{ }^{\circ}\text{C}$	$T_{RET} = +105\text{ }^{\circ}\text{C}$	10	-	-	

1. Guaranteed by characterization results.

2. Characterization is done according to JEDEC JESD22-A117.

Figure 17. I/O AC characteristics definition



6.3.14 NRST pin characteristics

The NRST pin input driver uses CMOS technology. It is connected to a permanent pull-up resistor, R_{PU} (see [Table 45](#))

Unless otherwise specified, the parameters given in [Table 45](#) are derived from tests performed under the conditions summarized in [Table 13](#).

Table 45. NRST pin characteristics

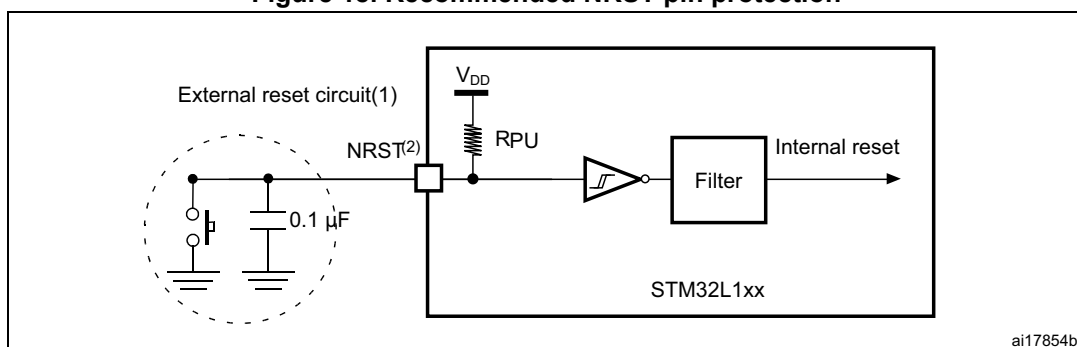
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{IL(NRST)}^{(1)}$	NRST input low level voltage	-	-	-	$0.3 V_{DD}$	V
$V_{IH(NRST)}^{(1)}$	NRST input high level voltage	-	$0.7 V_{DD}$	-	-	
$V_{OL(NRST)}^{(1)}$	NRST output low level voltage	$I_{OL} = 2 \text{ mA}$ $2.7 \text{ V} < V_{DD} < 3.6 \text{ V}$ $I_{OL} = 1.5 \text{ mA}$ $1.65 \text{ V} < V_{DD} < 2.7 \text{ V}$	-	-	0.4	
$V_{hys(NRST)}^{(1)}$	NRST Schmitt trigger voltage hysteresis	-	-	$10\% V_{DD}^{(2)}$	-	mV
R_{PU}	Weak pull-up equivalent resistor ⁽³⁾	$V_{IN} = V_{SS}$	30	45	60	k Ω
$V_{F(NRST)}^{(1)}$	NRST input filtered pulse	-	-	-	50	ns
$V_{NF(NRST)}^{(3)}$	NRST input not filtered pulse	-	350	-	-	ns

1. Guaranteed by design.

2. With a minimum of 200 mV.

3. The pull-up is designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance is around 10%.

Figure 18. Recommended NRST pin protection



1. The reset network protects the device against parasitic resets.
2. The user must ensure that the level on the NRST pin can go below the $V_{IL(NRST)}$ max level specified in [Table 45](#). Otherwise the reset will not be taken into account by the device.

6.3.15 TIM timer characteristics

The parameters given in the [Table 46](#) are guaranteed by design.

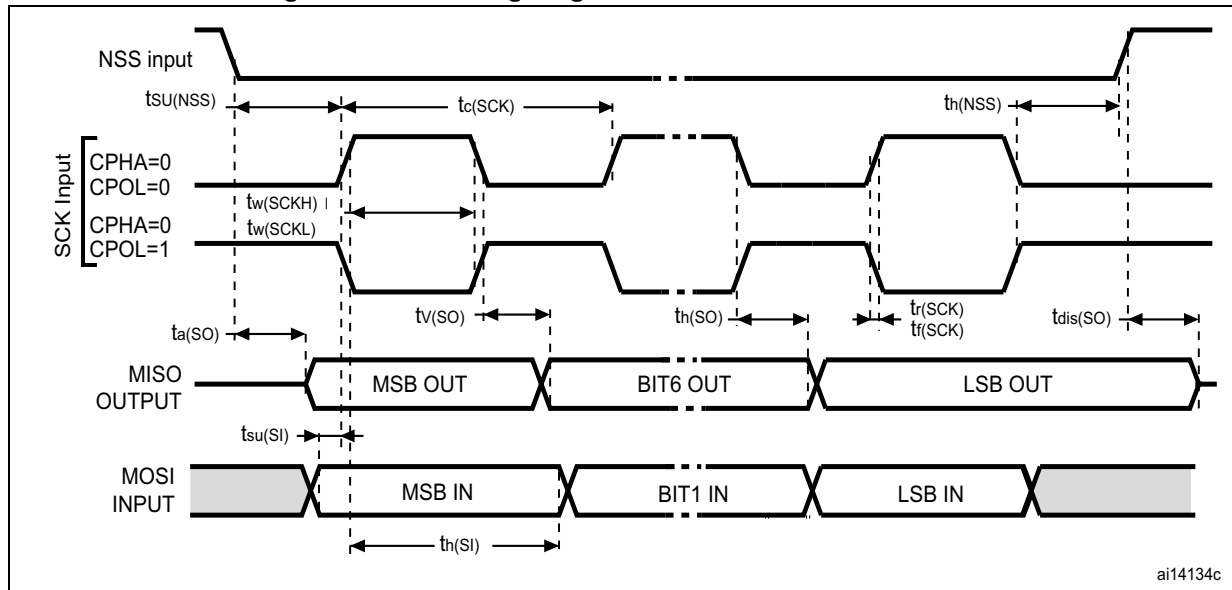
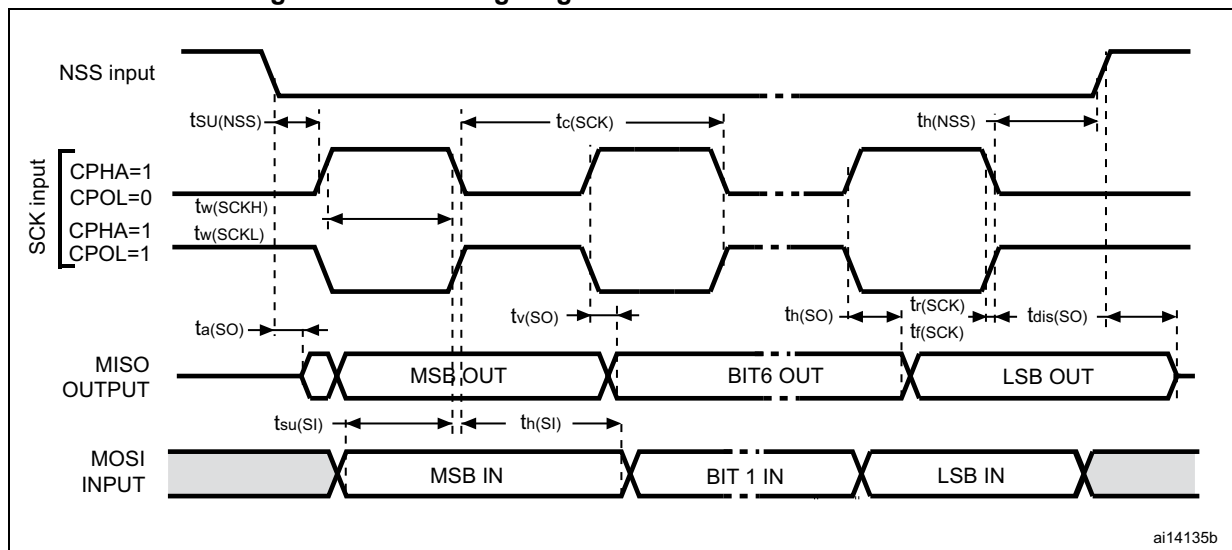
Refer to [Section 6.3.13: I/O port characteristics](#) for details on the input/output cition characteristics (output compare, input capture, external clock, PWM output).

Table 46. TIMx⁽¹⁾ characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
$t_{res(TIM)}$	Timer resolution time	-	1	-	$t_{TIMxCLK}$
		$f_{TIMxCLK} = 32 \text{ MHz}$	31.25	-	ns
f_{EXT}	Timer external clock frequency on CH1 to CH4	-	0	$f_{TIMxCLK}/2$	MHz
		$f_{TIMxCLK} = 32 \text{ MHz}$	0	16	MHz
Res_{TIM}	Timer resolution	-		16	bit
$t_{COUNTER}$	16-bit counter clock period when internal clock is selected (timer's prescaler disabled)	-	1	65536	$t_{TIMxCLK}$
		$f_{TIMxCLK} = 32 \text{ MHz}$	0.0312	2048	μs
t_{MAX_COUNT}	Maximum possible count	-	-	65536×65536	$t_{TIMxCLK}$
		$f_{TIMxCLK} = 32 \text{ MHz}$	-	134.2	s

1. TIMx is used as a general term to refer to the TIM2, TIM3 and TIM4 timers.

Figure 20. SPI timing diagram - slave mode and CPHA = 0

Figure 21. SPI timing diagram - slave mode and CPHA = 1⁽¹⁾

1. Measurement points are done at CMOS levels: $0.3V_{DD}$ and $0.7V_{DD}$.

Table 52. USB: full speed electrical characteristics (continued)

Driver characteristics ⁽¹⁾					
Symbol	Parameter	Conditions	Min	Max	Unit
t_{rfm}	Rise/ fall time matching	t_r/t_f	90	110	%
V_{CRS}	Output signal crossover voltage		1.3	2.0	V

1. Guaranteed by design.
2. Measured from 10% to 90% of the data signal. For more detailed informations, please refer to USB Specification - Chapter 7 (version 2.0).

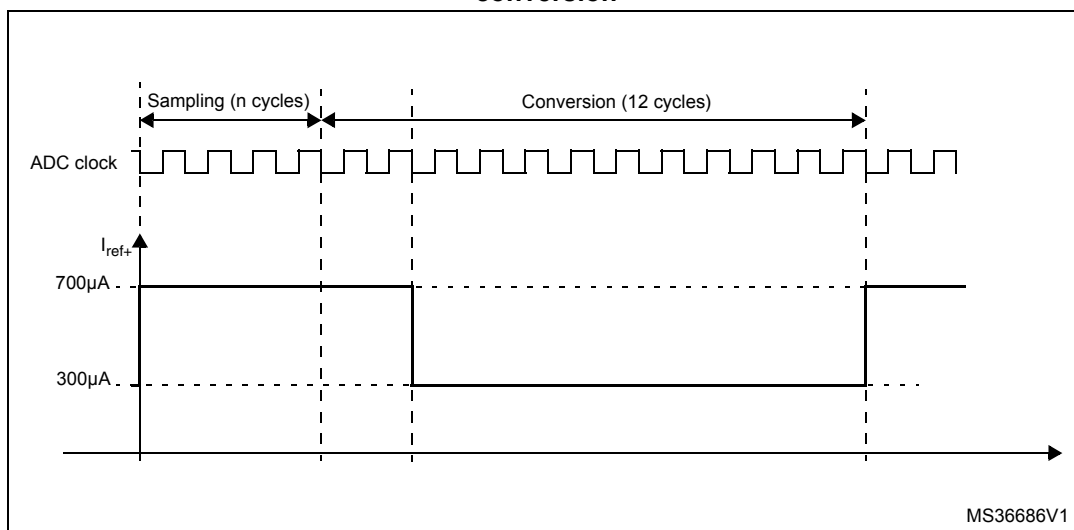
I2S characteristics

Table 53. I2S characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
f_{MCK}	I2S Main Clock Output		256 x 8K	256xFs ⁽¹⁾	MHz
f_{CK}	I2S clock frequency	Master data: 32 bits	-	64xFs	MHz
		Slave data: 32 bits	-	64xFs	
D_{CK}	I2S clock frequency duty cycle	Slave receiver, 48KHz	30	70	%
$t_{r(CK)}$	I2S clock rise time	Capacitive load CL=30pF	-	8	ns
$t_{f(CK)}$	I2S clock fall time			8	
$t_{v(WS)}$	WS valid time	Master mode	4	24	
$t_{h(WS)}$	WS hold time	Master mode	0	-	
$t_{su(WS)}$	WS setup time	Slave mode	15	-	
$t_{h(WS)}$	WS hold time	Slave mode	0	-	
$t_{su(SD_MR)}$	Data input setup time	Master receiver	8	-	
$t_{su(SD_SR)}$	Data input setup time	Slave receiver	9	-	
$t_{h(SD_MR)}$	Data input hold time	Master receiver	5	-	
$t_{h(SD_SR)}$		Slave receiver	4	-	
$t_{v(SD_ST)}$	Data output valid time	Slave transmitter (after enable edge)	-	64	
$t_{h(SD_ST)}$	Data output hold time	Slave transmitter (after enable edge)	22	-	
$t_{v(SD_MT)}$	Data output valid time	Master transmitter (after enable edge)	-	12	
$t_{h(SD_MT)}$	Data output hold time	Master transmitter (after enable edge)	8	-	

1. The maximum for 256xFs is 8 MHz

Note: Refer to the I2S section of the product reference manual for more details about the sampling frequency (Fs), f_{MCK} , f_{CK} and D_{CK} values. These values reflect only the digital peripheral behavior, source clock precision might slightly change them. D_{CK} depends mainly on the

Figure 28. Maximum dynamic current consumption on V_{REF+} supply pin during ADC conversion**Table 57. Maximum source impedance $R_{AIN\ max}^{(1)}$**

Ts (μs)	R _{AIN} max (kΩ)				Ts (cycles) f _{ADC} =16 MHz ⁽²⁾
	Multiplexed channels		Direct channels		
	2.4 V < V _{DDA} < 3.6 V	1.8 V < V _{DDA} < 2.4 V	2.4 V < V _{DDA} < 3.6 V	1.8 V < V _{DDA} < 2.4 V	
0.25	Not allowed	Not allowed	0.7	Not allowed	4
0.5625	0.8	Not allowed	2.0	1.0	9
1	2.0	0.8	4.0	3.0	16
1.5	3.0	1.8	6.0	4.5	24
3	6.8	4.0	15.0	10.0	48
6	15.0	10.0	30.0	20.0	96
12	32.0	25.0	50.0	40.0	192
24	50.0	50.0	50.0	50.0	384

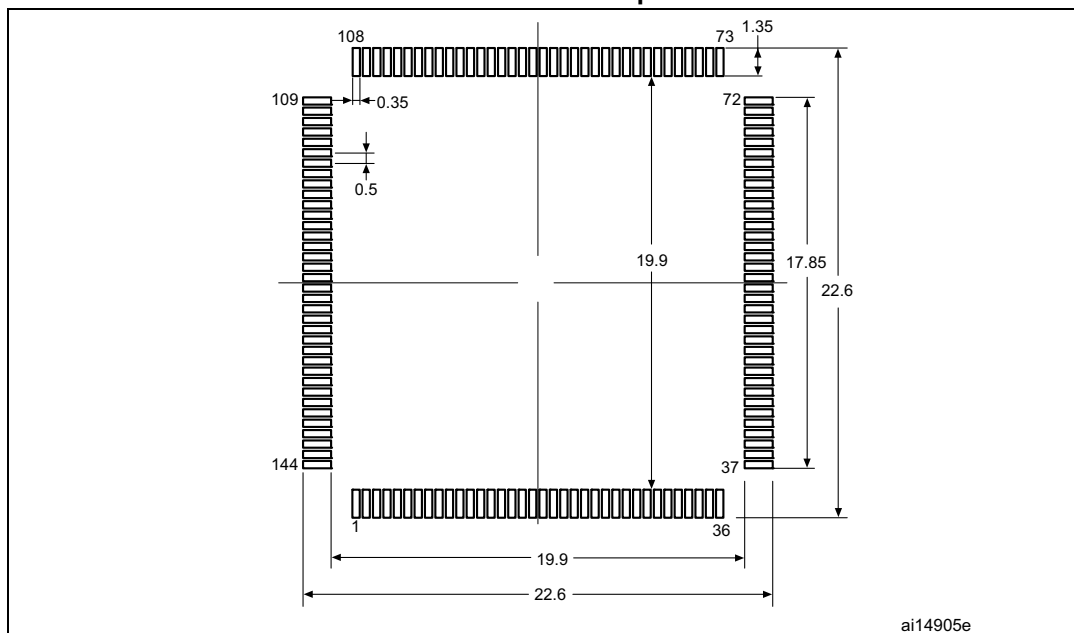
1. Guaranteed by design.

2. Number of samples calculated for $f_{ADC} = 16\ MHz$. For $f_{ADC} = 8$ and $4\ MHz$ the number of sampling cycles can be reduced with respect to the minimum sampling time T_s (μs),

General PCB design guidelines

Power supply decoupling should be performed as shown in [Figure 10](#). The applicable procedure depends on whether V_{REF+} is connected to V_{DDA} or not. The $100\ nF$ capacitors should be ceramic (good quality). They should be placed as close as possible to the chip.

Figure 31. LQFP144, 20 x 20 mm, 144-pin low-profile quad flat package recommended footprint

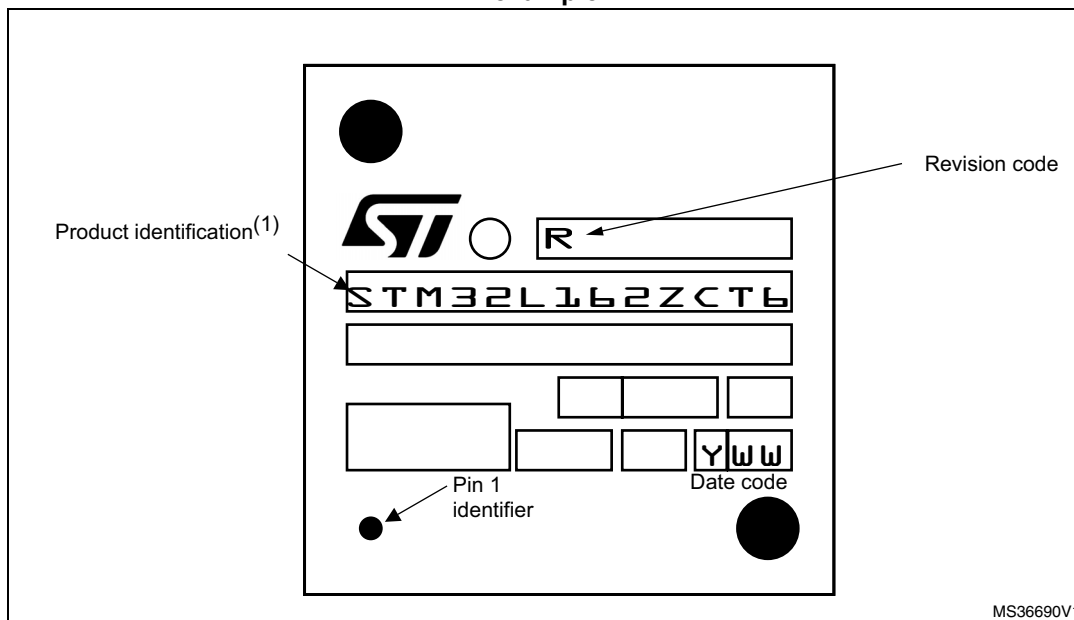


1. Dimensions are in millimeters.

Marking of engineering samples

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Figure 32. LQFP144, 20 x 20 mm, 144-pin low-profile quad flat package top view example

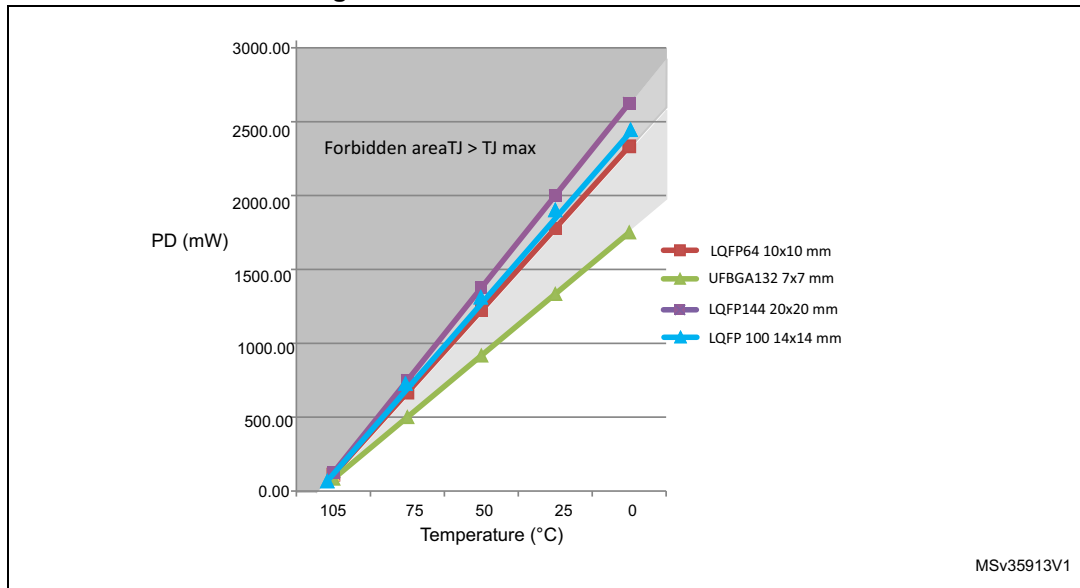


1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
E3	-	7.500	-	-	0.2953	-
e	-	0.500	-	-	0.0197	-
K	0°	3.5°	7°	0°	3.5°	7°
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
ccc	-	-	0.080	-	-	0.0031

[illegible]

Figure 43. Thermal resistance suffix 7



7.5.1 Reference document

JESD51-2 Integrated Circuits Thermal Test Method Environment Conditions - Natural Convection (Still Air). Available from www.jedec.org.